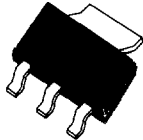


CZT2955 PNP
CZT3055 NPN

2.0W SURFACE MOUNT
COMPLEMENTARY SILICON
POWER TRANSISTOR

POWER™
223



SOT-223 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZT2955 and CZT3055 types are surface mount epoxy molded complementary silicon transistors manufactured by the epitaxial base process, designed for surface mounted power amplifier applications up to 6.0 amps.

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

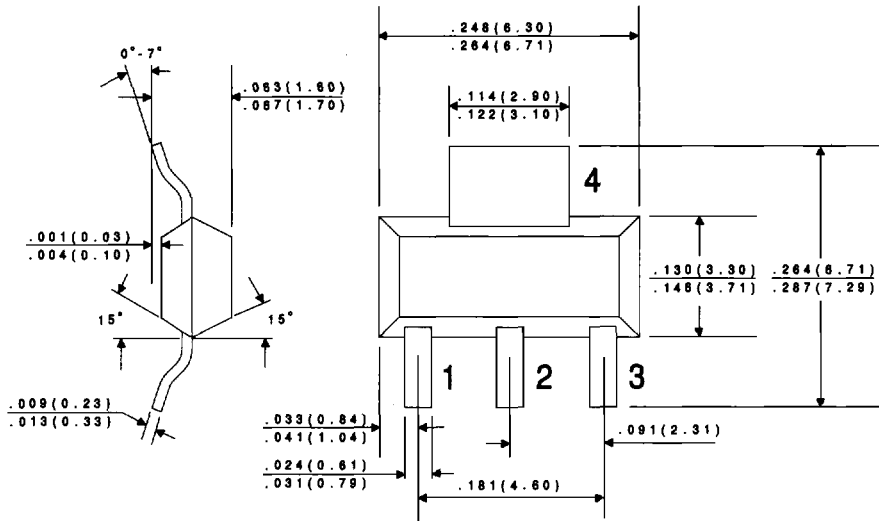
	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CER}	70	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	7.0	V
Collector Current	I_C	6.0	A
Base Current	I_B	3.0	A
Power Dissipation	P_D	2.0	W
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	62.5	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CEO}	$V_{CE}=30\text{V}$		700	μA
I_{CEV}	$V_{CE}=100\text{V}, V_{EB}(\text{off})=1.5\text{V}$		1.0	mA
I_{EBO}	$V_{EB}=7.0\text{V}$		5.0	mA
BV_{CER}	$I_C=30\text{mA}, R_{BE}=100\Omega$	70		V
BV_{CEO}	$I_C=30\text{mA}$	60		V
* $V_{CE}(\text{SAT})$	$I_C=4.0\text{A}, I_B=400\text{mA}$		1.1	V
* $V_{BE}(\text{ON})$	$V_{CE}=4.0\text{V}, I_C=4.0\text{A}$		1.5	V
* h_{FE}	$V_{CE}=4.0\text{V}, I_C=4.0\text{A}$	20	70	
* h_{FE}	$V_{CE}=4.0\text{V}, I_C=6.0\text{A}$	5.0		
f_T	$V_{CE}=10\text{V}, I_C=500\text{mA}, f=1.0\text{MHz}$	2.5		MHz

* Pulsed, 2% D.C.

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) COLLECTOR
- 3) EMITTER
- 4) COLLECTOR

DATA SHEET

R1